Silicon PNP Power Transistor 2SB885

DESCRIPTION

·With TO-220C package
·DARLINGTON
·High DC durrent gain
·Low collector saturation voltage
·Complement to type 2SD1195

APPLICATIONS

·For motor drivers,printer hammer drivers,relay drivers,voltage regulator control applications

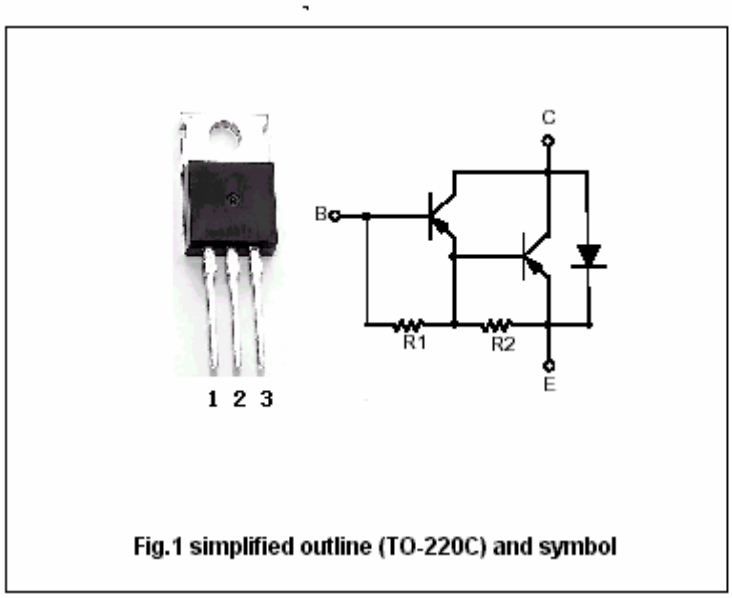

Fig.1 simplified outline (TO-220C) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings(Tc=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-110	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current-DC		-5	A
I_{CM}	Collector current-Pulse		-8	A
P_C	Collector power dissipation	T_C=25□	35	W
		T_a=25□	1.75	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-50mA, R_{BE}=∞	-100			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-5mA, I_E=0	-110			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-2.5A ,I_B=-5mA			-1.5	V
$V_{BE\ sat}$	Base-emitter saturation voltage	I_C=-2.5A ,I_B=-5mA			-2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=-80V, I_E=0			-0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-3.0	mA
h_{FE}	DC current gain	I_C=-2.5A ; V_{CE}=-3V	1500			
f_T	Transition frequency	V_{CE}=-5V, I_C=-2.5A		20		MHz

Switching times

t_{on}	Turn-on time	I_C=-2A ; V_{CC}=-50V I_{B1}=-I_{B2}=-4mA;R_L=25Ω		0.7		μs
t_{stg}	Storage time			1.3		μs
t_f	Turn-off time			1.5		μs

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PACKAGE OUTLINE

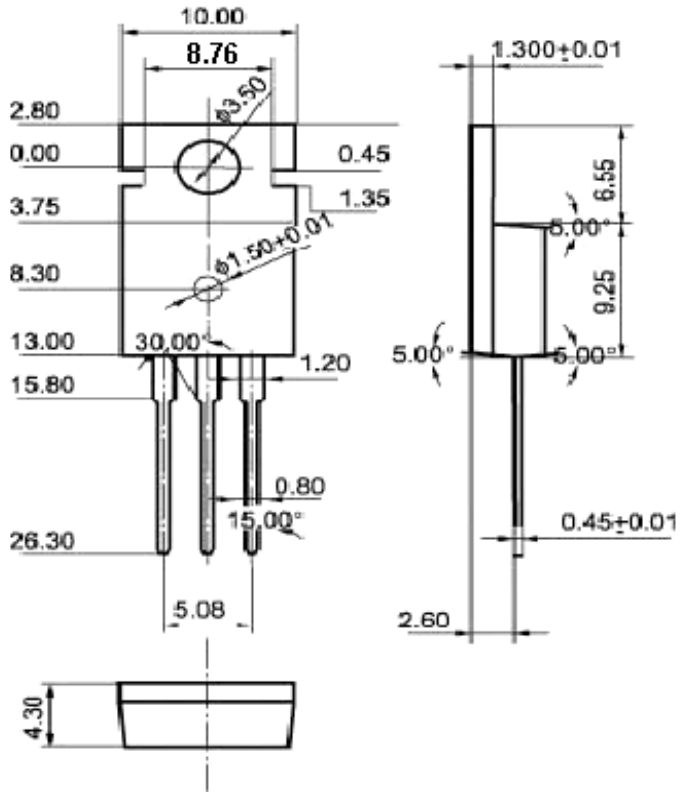

Fig.2 Outline dimensions